



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	3	Α
Peak Pulse Current	I _{CM}	6	A
Base Current	I _B	0.5	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	(Note 6)		3.2	
Power Dissipation	(Note 7)	P_{D}	1.7	W
	(Note 8)		0.74	
	(Note 6)		39	
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ heta JA}$	75	
	(Note 8)		169	°C/W
Thermal Resistance, Junction to Leads	(Note 9)	R _{0JL}	9	
Thermal Resistance, Junction to Case	(Note 10)	$R_{ heta JC}$	10	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 11)

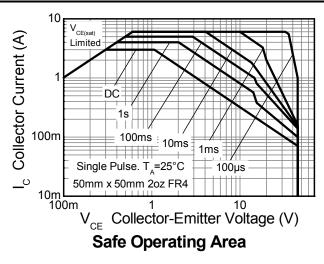
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

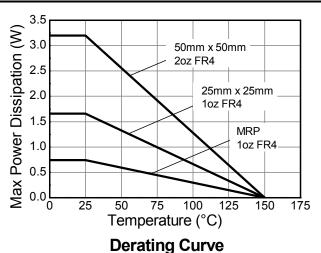
Notes:

- 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper under still air conditions whilst operating in a steady-state.
 Same as note (6), except mounted on 25mm x 25mm 1oz copper.
 Same as note (6), except mounted on minimum recommended pad (MRP) layout.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Thermal resistance from junction to the top of the case.
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

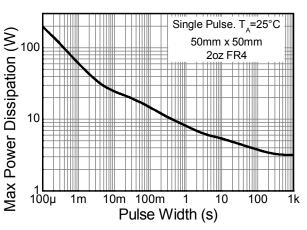


Thermal Characteristics and Derating Information

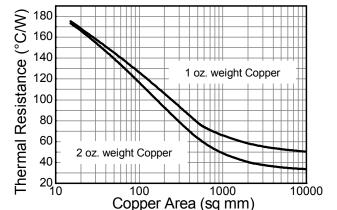




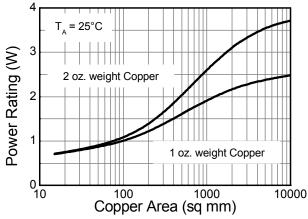
20 D=0.5 Single Pulse D=0.05 D=0.1 100 1k Pulse Width (s)



Transient Thermal Impedance



Pulse Power Dissipation



Thermal Resistance vs. Cu Area

Power Rating vs. Cu Area





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

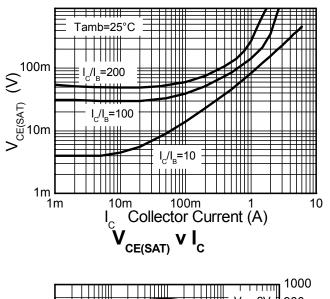
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	60	145	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	45	65	_	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.2	_	V	$I_E = 100 \mu A, I_C = 0$
Collector-Base Cutoff Current	I _{CBO}	_	<1	20	nA	$V_{CB} = 35V, I_{E} = 0$
Collector-Emitter Cutoff Current	I _{CES}	_	<1	20	nA	V _{CB} = 35V, V _{BE} = 0
Emitter-Base Cutoff Current	I _{EBO}	_	<1	20	nA	V _{EB} = 5.6V, I _C = 0
ON CHARACTERISTICS (Note 12)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_ _ _ _	50 240 210 230	85 360 320 350	mV	I_C = 100mA, I_B = 0.5mA I_C = 1A, I_B = 5mA I_C = 2A, I_B = 40mA I_C = 3A, I_B = 150mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	1.0	1.2	V	I _C = 3A, I _B = 150mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	0.9	1.1	V	$I_C = 3A$, $V_{CE} = 2V$
DC Current Gain	h _{FE}	500 400 150 60	700 600 350 120	_ _ _ _	ı	I _C = 100mA, V _{CE} = 2V I _C = 1A, V _{CE} = 2V I _C = 2A, V _{CE} = 2V I _C = 3A, V _{CE} = 2V
AC CHARACTERISTICS						
Transition Frequency	f _T	150		_	MHz	I_C = 50mA, V_{CE} = 5V, f = 50MHz
Output Capacitance	C _{obo}	_	16	_	pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{on} t _{off}	_	33 1300	_	ns ns	V _{CC} = 10V, I _C = 500mA, I _{B1} = -I _{B2} = 50mA

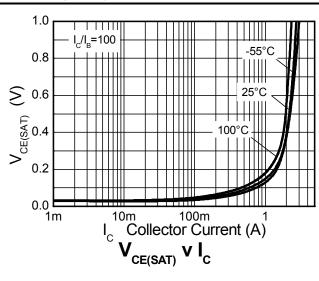
Note:

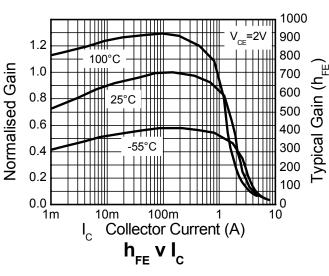
12. Pulse Test: Pulse width ≤300µs. Duty cycle ≤2.0%.

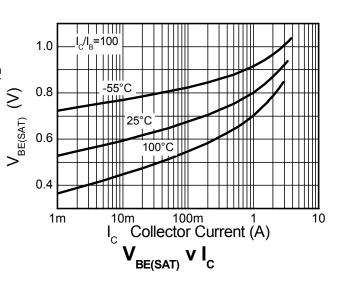


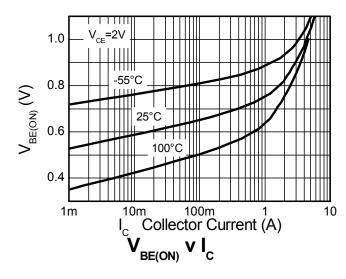
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







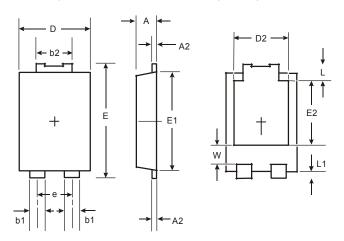






Package Outline Dimensions

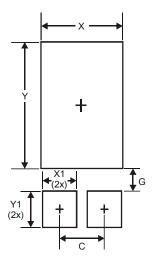
 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ latest \ version.$



POWERDI5					
Dim	Min	Max			
Α	1.05	1.15			
A2	0.33	0.43			
b1	0.80	0.99			
b2	1.70	1.88			
D	3.90	4.05			
D2	3.054 Typ				
Е	6.40	6.60			
е	1.84 Typ				
E1	5.30	5.45			
E2	3.549 Typ				
١	0.75	0.95			
L1	0.50	0.65			
W	1.10	1.41			
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.840
G	0.852
X	3.360
X1	1.390
Y	4.860
Y1	1 400





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